

Features

- Frequency: 12.7GHz~15.5GHz
- Small Signal Gain: 20dB
- Output P_{-1dB}: 39dBm
- PAE: 35%@P_{-1dB}, f=14GHz
- IM₃: -25dBc, 30dBm/Tone@14GHz
- Die size: 4.1mm×4.5mm×0.1mm
- Supply Voltage: +8V/-V_g
- Packaged: Bare Die

Typical Applications

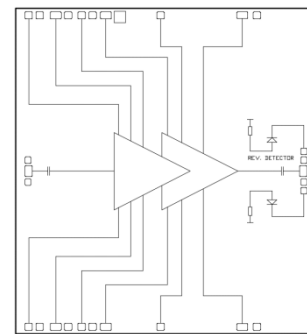
- Point-to-Point Radios
- SATCOM
- Military and Space
- Radar

General Description

SAC3151 is a Ku-band GaAs MMIC power amplifier. SAC3151 provides 20 dB of gain, and 39dBm of output power for 1 dB compression and 35% PAE from +8V supply.

The chip has surface passivation for protection and backside via holes and gold metallization to allow a conductive epoxy die attach process.

Functional Diagram



Electrical Performance

T_A=25°C, V_D=+8V, I_{DQ}=2.2A, Z₀=50Ω, CW

Parameter	Min.	Typ.	Max.	Units
Frequency Range	12.7	—	15.5	GHz
Small Signal Gain	16	20	—	dB
Small Signal Gain Flatness	—	±1.5	—	dB
Reverse Isolation	—	-65	—	dB
RF Input VSWR	—	1.8	—	:1
Output P _{-1dB}	37.5	39	—	dBm
IM ₃ *	—	25	—	dBc
Drain Voltage (V _D)	8	—	8.5	V
Gate Current	—	2	22	mA
Supply Current (I _D)***	—	—	5	A
Thermal Resistance**	—	2.8	—	°C/W

* P_{out}/Tone= 30dBm, f_c = 14GHz, Δf = 4MHz

** Measurement taken at P_{out} = OP_{-1dB}, IR method. 100% DC power is dissipated on the device the thermal resistance is 3.1°C/W

*** Adjust V_g between -1.5V to -0.4V to achieve I_{DQ}= 2.2A , and typical V_g voltage is -0.8V.

Absolute Maximum Ratings

Maximum Input Power	+25dBm	Operating Temperature (Backside)	-55°C~+85°C
Channel Temperature	150°C	Storage Temperature	-55°C~+150°C
Maximum V _D	+8.5V	V _G Range	-3V~-0.4V

SAC3151



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12.7GHz~15.5GHz 39dBm

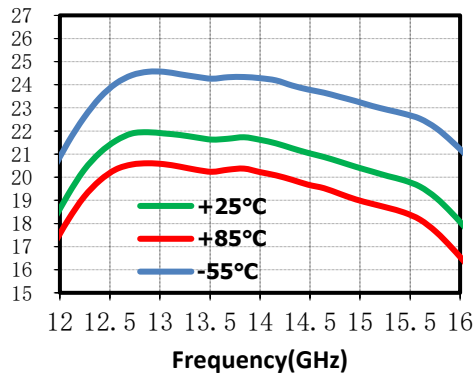
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Typical Performance Curve

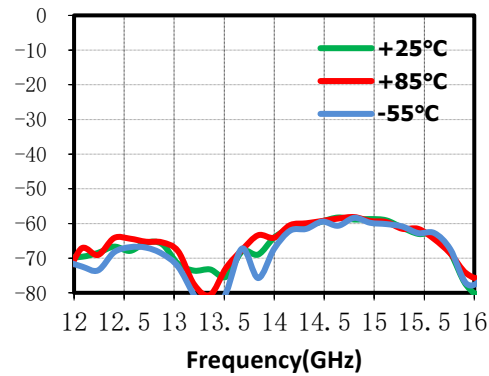
The following data are obtained by SAC3151 evaluation board

$V_D = +8V, I_{DQ} = 2.2A, CW, T_A = +25^\circ C$

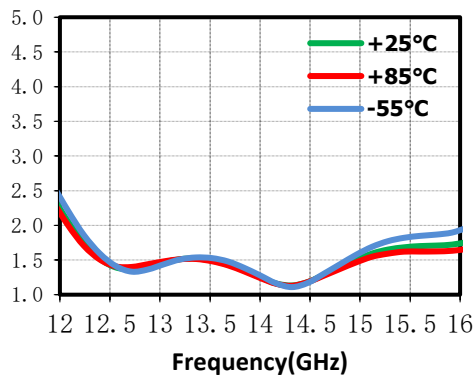
Small Signal Gain(dB) vs. Temperature



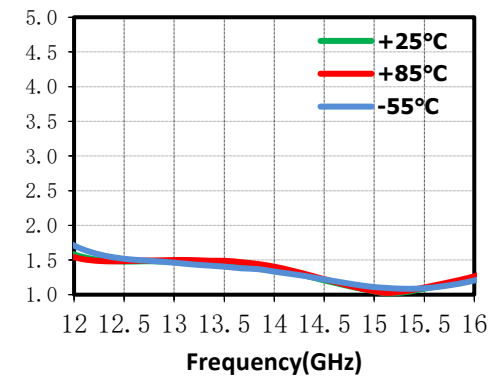
Isolation(dB) vs. Temperature



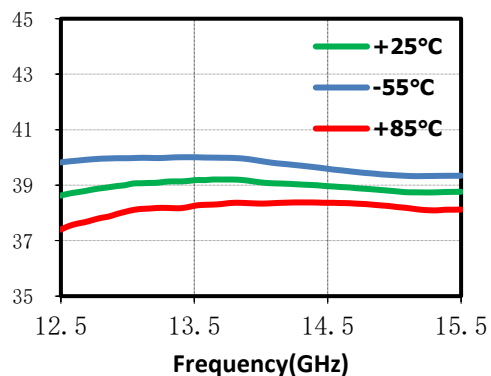
RF Input VSWR (:1) vs. Temperature



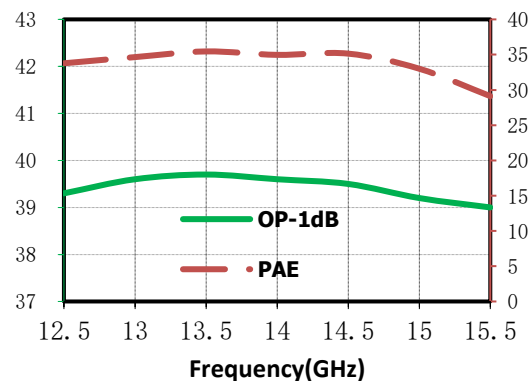
RF Output VSWR (:1) vs. Temperature



Output P_{1dB}(dBm) vs. Temperature



OP_{1dB}(dBm), PAE vs. Frequency



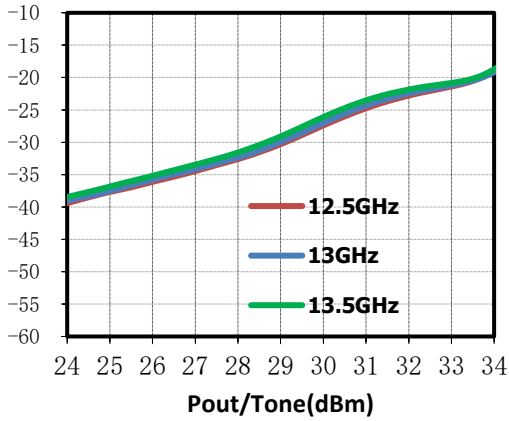
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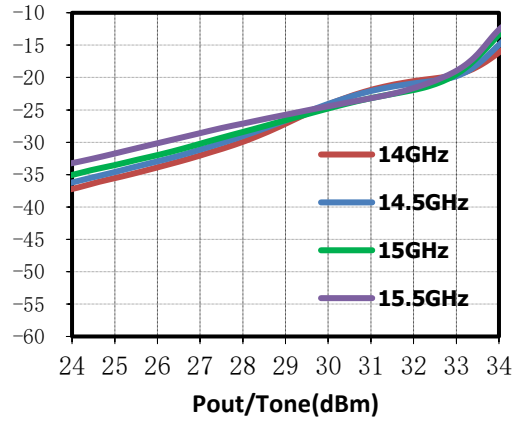
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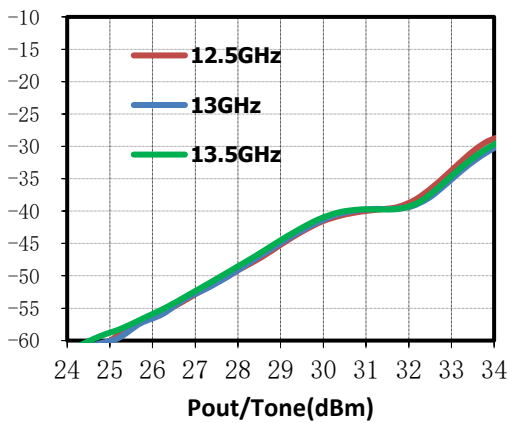
IM₃(dBc) vs. Pout/Tone



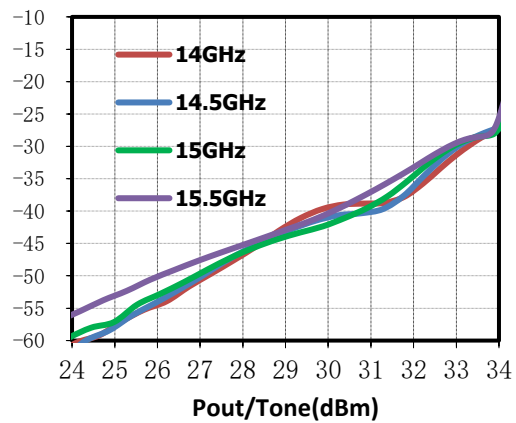
IM₃(dBc) vs. Pout/Tone



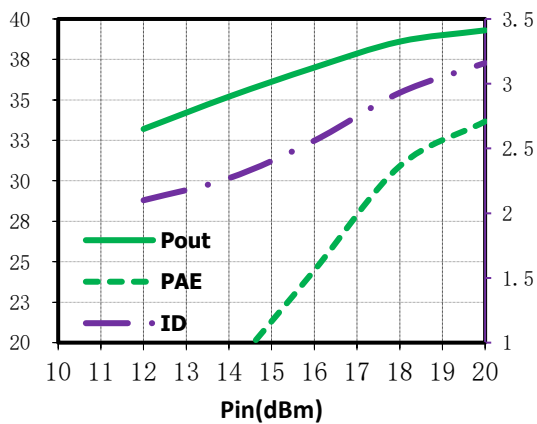
IM₅(dBc) vs. Pout/Tone



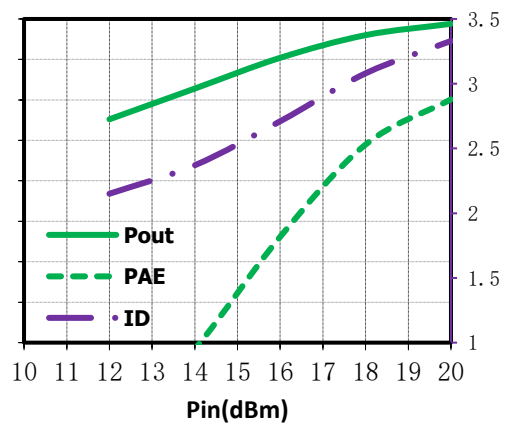
IM₅(dBc) vs. Pout/Tone



Pout(dBm), PAE(%), ID(A) vs. Pin, f=12.5GHz



Pout(dBm), PAE(%), ID(A) vs. Pin, f=13GHz



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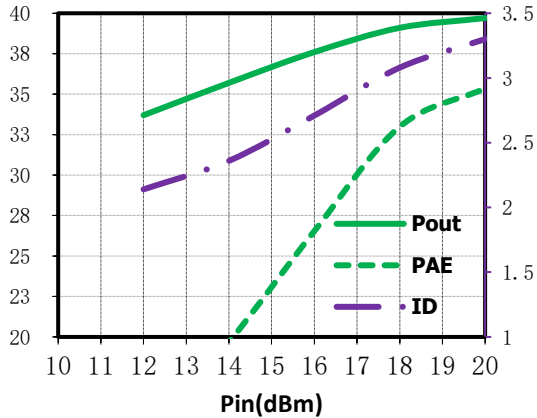
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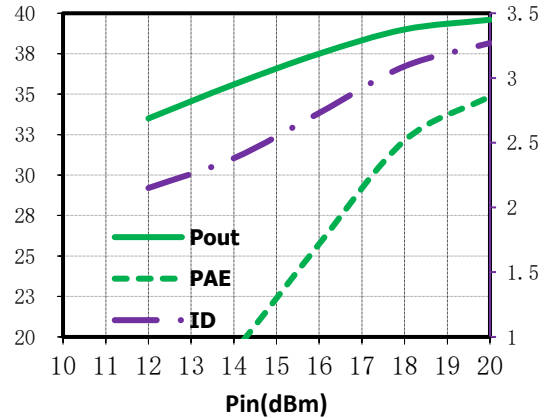
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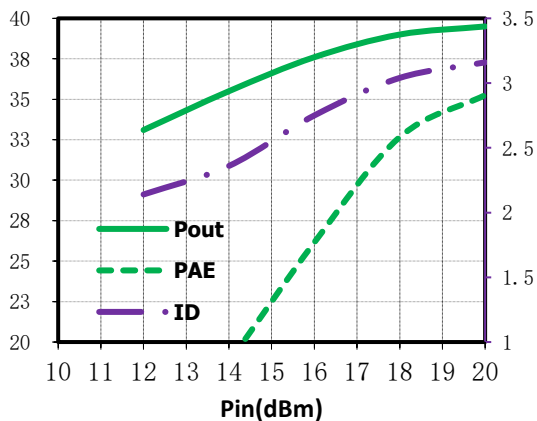
Pout(dBm)、PAE(%)、ID(A) vs. Pin, f=13.5GHz



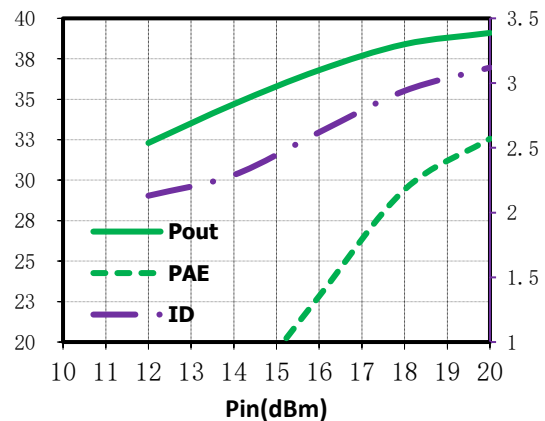
Pout(dBm)、PAE(%)、ID(A) vs. Pin, f=14GHz



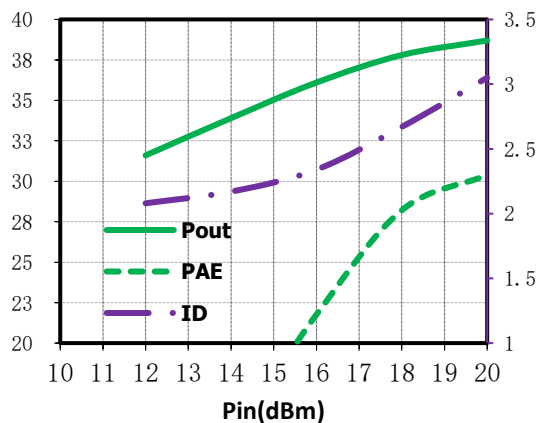
Pout(dBm)、PAE(%)、ID(A) vs. Pin, f=14.5GHz



Pout(dBm)、PAE(%)、ID(A) vs. Pin, f=15GHz



Pout(dBm)、PAE(%)、ID(A) vs. Pin, f=15.5GHz



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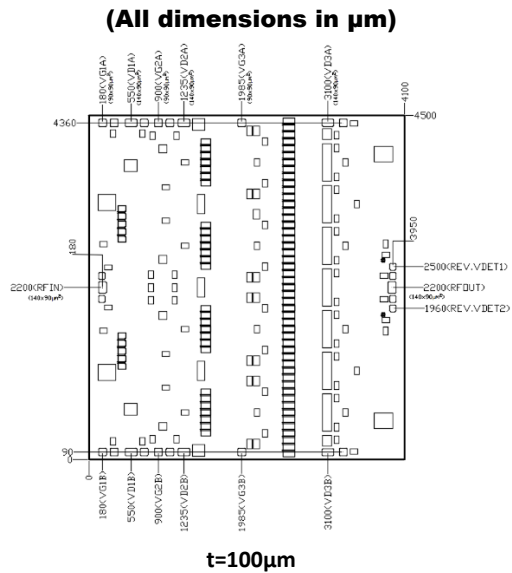
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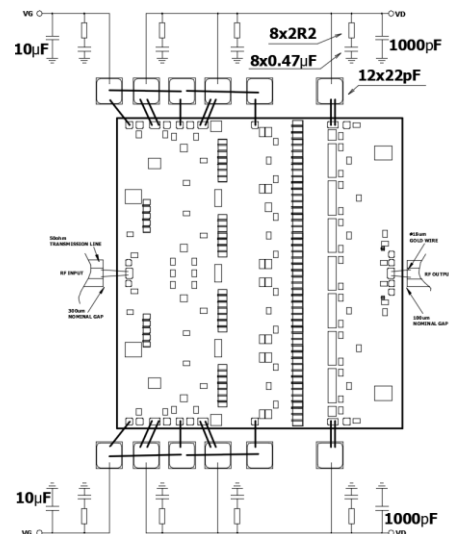
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Die Outline



Assembly Diagram



Attention:

1. SAC3151 requires drain positive voltage (VDx) and gate negative voltage (VGx) bias, which shall be applied before applying drain positive voltage. Ensure that the gate negative voltage is applied;
2. Vacuum AuSn eutectic soldering is recommended;
3. The single-layer decoupling capacitor shall be of small volume and thin dielectric type as far as possible;
4. When using drain pulse voltage modulation, ensure that the maximum overshoot voltage does not exceed 8.5V.

Revision History

Revision	Date	Comment
1.0	December 1, 2022	First Release

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